



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: 10/625,065

Confirmation Number: 8265

Applicant: Jong-Jan Lee *et al.*

Filed: July 22, 2003

Group #: 1763

Examiner: George A. Goudreau

Docket No: SLA.0696

Customer No: 55376

For: FABRICATION OF SILICON-ON-NOTHING (SON) MOSFET
FABRICATION USING SELECTIVE ETCHING OF $\text{Si}_{1-x}\text{Ge}_x$ LAYER

MS AMENDMENT

Commissioner for Patents

P.O. Box 1450

Alexandria, Virginia 22313-1450

RESPONSE TO OFFICE ACTION UNDER 37 C.F.R. § 1.111

Introductory Comments

In response to the Office Action dated July 7, 2005, please amend the above-identified Application as follows:

Amendment to the Specification None

Amendment to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Amendment to the Drawings None

Remarks/Arguments begin on page 5 of this paper.

An **Appendix** is not included.

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